

ABSTRACT**Multi-Layer Structures and Process for
Fabricating Semiconductor Devices**

The present invention relates to a method comprising providing a Silicon-On-Insulator, SOI, stack comprising a substrate layer, a first oxide layer on the substrate layer and a silicon layer on the first oxide layer (BOX layer), forming at least one first region of the SOI stack wherein the silicon layer is thinned by thermally oxidizing a part of the silicon layer and forming at least one second region of the SOI stack wherein the first oxide layer (BOX layer) is thinned by annealing.

Fig. 1f